

Titre: Disorder semiconductor alloys: physics, devices and metallurgy

1. Organisateurs (avec affiliation, usuellement 2 ou 3 personnes) :

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2. Parrainage ou lien avec des sociétés savantes, des GDR ou autres structures

RéMiSol - Réseau Microscopies à Sondes Locales.

NS-CPU - Nanosciences with near-field microscopy under ultra-high vacuum

SFP - Société Française de Physique

EPS - European Physical Society

3. Résumé de la thématique du minicolloque :

Alloying of semiconductors is routinely used to engineer the desired bandgap of a range of materials for opto-electronic and photo-voltaic applications [1]. The random placement of the constituent atoms in the crystal lattice, known as intrinsic alloy disorder [2], is unavoidable and can significantly modify the local opto-electronic properties at the scale of the disorder. Depending on the details of the application, these modifications can be beneficial or problematic for device performance. Either way, a variety of novel physical phenomena can be directly or indirectly related to alloy disorder.

The present mini-colloque will focus on physical phenomena related to alloy and compositional disorder in a range of technologically relevant materials systems, from III-V semiconductors [3] and 2D transition metal dichalcogenide alloys [4] to organic semiconductors and perovskites [5,6]. Quantum properties of the localized states resulting from potential fluctuations at the nm scale, the metallurgy of intrinsic alloy disorder, and the consequences for device applications will be discussed.

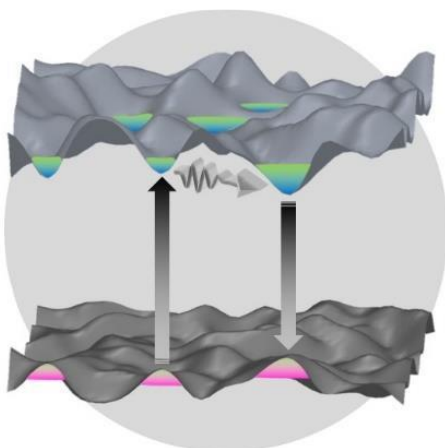


Figure 1: In-plane disordered electron and hole effective energy levels with localization landscape.

¹C. Weisbuch et. al, Nanophotonics **10**, 3 (2021)

²L. Rigutti et al., J. Appl. Phys. **119**, 105704 (2016)

³M. Piccardo et al., Phys. Rev. B **95**, 144205 (2017)

⁴H. Masenda et al., Adv. Electron. Mater. 2100196 (2021)

⁵J.C. Blancon et al., Nature Nanotech. **15**, 969 (2020)

⁶X.-G. Zhao et al., Materials Today **49**, 107 (2021)